

國立中央大學八十三學年度研究所碩士班入學試題卷

系所別：光電科學研究所 組 科目：材料工程 共 / 頁 頁

1. The extra energy required to move an interstitial atom between two other atoms is found to be 1.0ev. If one atom out of 10^{20} atoms in a metal has this much additional energy at 20°C, what fraction of the atoms will have 1.0ev additional energy at 1000°C. (20%)

[Hint: $1\text{ev} = 1.6 \times 10^{-12} \text{ erg}$, Boltzmann's constant $K = 1.38 \times 10^{-16} \text{ erg/atom}^{\circ}\text{k}$]

2. An intrinsic Semiconductor has a resistivity of 1.20 ohm.cm at 20°C and 1.08 ohm.cm at 50°C. Estimate the value of the energy gap. (Assume negligible change in mobility over this small temperature range) (20%)

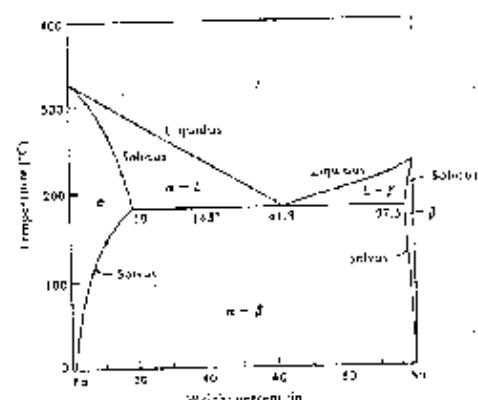
3. Consider the polymorphic transformation A=B. The interface energy between A and B is 500 ergs/cm², and the values of the change in free energy per unit volume ΔF_v for A \rightarrow B are -100 cal/cm³ at 1000°C and -500 cal/cm³ at 900°C (1cal/cm³ = 4.185×10^7 ergs/cm³). (20%)

(a) Determine the critical nucleus radius for the nucleation of B within A at each temperature

(b) Calculate the energy that must be supplied for reaction to proceed in each case.

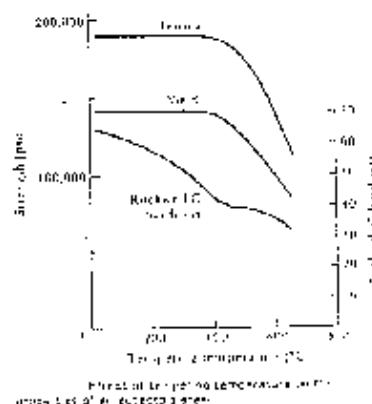
4. For a Pb-30% Sn alloy, determine the phase present, their amounts and compositions at 300°C, 200°C, 184°C, 182°C and 0°C.

(20%)



5. We would like to produce an eutectoid steel that has a maximum yield strength of 100,000 psi with a maximum hardness of Rc40. What tempering temperature would you recommend?

(20%)



Infrared Intensity vs. Temperature (infrared light absorbed after reflection from the eutectoid steel)

